

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-41.(Cancelled)

42.(Currently Amended) A display device comprising:

a silicon semiconductor substrate;

an insulating layer formed on the silicon semiconductor substrate;

a field effect transistor formed on the insulating layer;

an interlayer insulating film formed over the field effect transistor;

an EL element formed on the interlayer insulating film, the EL element comprising a pair of electrodes and an EL layer interposed therebetween,

wherein one of the pair of electrodes is electrically connected to the field effect transistor

a switching transistor and a current controlling transistor formed on the insulating layer, each

comprising a source region, a drain region, a gate electrode and a gate insulating film;

an electrode electrically connected with one of the source region and the drain region of the
switching transistor;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region
of the current controlling transistor, and formed on the dielectric layer;

a first electrode electrically connected with the other one of the source region and the drain
region of the current controlling transistor;

an organic EL layer formed over the first electrode; and
a second electrode formed over the organic EL layer.

43.(Currently Amended) A display device according to claim 42, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

44.(New) A display device according to claim 42, wherein the first electrode overlaps the power supply line.

45.(New) A display device according to claim 42, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

46.(New) A display device according to claim 42, wherein the dielectric layer comprises an oxidation film of the electrode.

47.(New) A display device comprising:
a semiconductor substrate;
an insulating layer formed on the semiconductor substrate;
a p-channel type switching transistor and an n-channel type current controlling transistor formed on the insulating layer, each comprising a source region, a drain region, a gate electrode and

a gate insulating film;

an electrode electrically connected with one of the source region and the drain region of the p-channel type switching transistor;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;

a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;

an organic EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

48.(New) A display device according to claim 47, wherein the first electrode overlaps the power supply line.

49.(New) A display device according to claim 47, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

50.(New) A display device according to claim 47, wherein the dielectric layer comprises an oxidation film of the electrode.

51.(New) A display device according to claim 47, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

52.(New) A display device comprising:

- a semiconductor substrate;
- a switching transistor and a current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an electrode electrically connected with one of the source region and the drain region of the switching transistor;
- a dielectric layer formed on the electrode;
- a power supply line electrically connected with one of the source region and the drain region of the current controlling transistor, and formed on the dielectric layer;
- a first electrode electrically connected with the other one of the source region and the drain region of the current controlling transistor;
- an organic EL layer formed over the first electrode; and
- a second electrode formed over the organic EL layer.

53.(New) A display device according to claim 52, wherein the first electrode overlaps the power supply line.

54.(New) A display device according to claim 52, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

55.(New) A display device according to claim 52, wherein the dielectric layer comprises an oxidation film of the electrode.

56.(New) A display device according to claim 52, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

57.(New) A display device comprising:

- a semiconductor substrate;
- a p-channel type switching transistor and an n-channel type current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an electrode electrically connected with one of the source region and the drain region of the p-channel type switching transistor;
- a dielectric layer formed on the electrode;
- a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;
- a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;

an organic EL layer formed over the first electrode; and
a second electrode formed over the organic EL layer.

58.(New) A display device according to claim 57, wherein the first electrode overlaps the power supply line.

59.(New) A display device according to claim 57, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

60.(New) A display device according to claim 57, wherein the dielectric layer comprises an oxidation film of the electrode.

61.(New) A display device according to claim 57, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

62.(New) A display device comprising:
a semiconductor substrate;
a switching transistor and a current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
an electrode electrically connected with one of the source region and the drain region of the switching transistor;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the current controlling transistor, and formed on the dielectric layer;

a storage capacitance comprising the electrode, the dielectric layer and the power supply line;

a first electrode electrically connected with the other one of the source region and the drain region of the current controlling transistor;

an organic EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

63.(New) A display device according to claim 62, wherein the first electrode overlaps the power supply line.

64.(New) A display device according to claim 62, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

65.(New) A display device according to claim 62, wherein the dielectric layer comprises an oxidation film of the electrode.

66.(New) A display device according to claim 62, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

67.(New) A display device comprising:

- a semiconductor substrate;
- a p-channel type switching transistor and an n-channel type current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an electrode electrically connected with one of the source region and the drain region of the p-channel type switching transistor;
- a dielectric layer formed on the electrode;
- a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;
- a storage capacitance comprising the electrode, the dielectric layer and the power supply line;
- a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;
- an organic EL layer formed over the first electrode; and
- a second electrode formed over the organic EL layer.

68.(New) A display device according to claim 67, wherein the first electrode overlaps the power supply line.

69.(New) A display device according to claim 67, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

70.(New) A display device according to claim 67, wherein the dielectric layer comprises an oxidation film of the electrode.

71.(New) A display device according to claim 67, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.